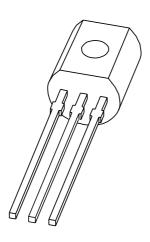
DISCRETE SEMICONDUCTORS

DATA SHEET



PSS8050 NPN medium power 25 V transistor

Product specification Supersedes data of 2002 Nov 18





NPN medium power 25 V transistor

PSS8050

FEATURES

- · High total power dissipation
- · High current capability.

APPLICATIONS

- · Medium power switching and muting
- Amplification
- Portable radio output amplifier (class-B, push-pull).

DESCRIPTION

NPN transistor in a SOT54 (TO-92) plastic package. PNP complement: PSS8550.

MARKING

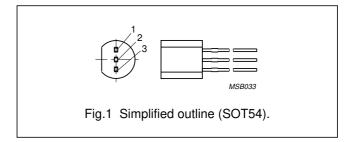
TYPE NUMBER	MARKING CODE
PSS8050C	S8050C
PSS8050D	S8050D

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	25	٧
I _C	collector current (DC)	1.5	Α

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	٧
V_{CEO}	collector-emitter voltage	open base	_	25	V
V _{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current (DC)		_	1.5	Α
I _{CM}	peak collector current		_	2	Α
I _B	base current (DC)		_	300	mA
I _{BM}	peak base current		_	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	850	mW
		T _{amb} ≤ 25 °C; note 2	_	900	mW
		T _{amb} ≤ 25 °C; note 3	_	1	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
- 2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².
- 3. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint. Operated under pulsed conditions: pulse width $t_p \le 1$ s; duty cycle $\delta \le 0.75\%$.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	147	K/W
		in free air; note 2	139	K/W
		in free air; note 3	125	K/W

Notes

- 1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
- 2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².
- 3. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint. Operated under pulsed conditions: pulse width $t_p \le 1$ s; duty cycle $\delta \le 0.75\%$.

CHARACTERISTICS

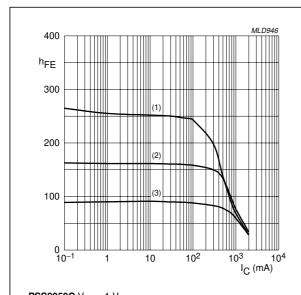
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 35 V; I _E = 0	_	_	100	nA
		V _{CB} = 35 V; I _E = 0; T _{amb} = 150 °C	_	_	50	μΑ
I _{CEO}	collector-emitter cut-off current	V _{CE} = 25 V; I _B = 0	_	_	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 6 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	I _C = 5 mA; V _{CE} = 1 V	45	_	_	
		$I_C = 800 \text{ mA}; V_{CE} = 1 \text{ V}$	40	_	_	
	DC current gain	I _C = 100 mA; V _{CE} = 1 V				
	PSS8050C		120	_	200	
	PSS8050D		160	-	300	
V _{CEsat}	collector-emitter saturation voltage	I _C = 800 mA; I _B = 80 mA	_	165	500	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 800 mA; I _B = 80 mA	_	_	1.2	V
V _{BEon}	base-emitter turn-on voltage	I _C = 10 mA; V _{CE} = 1 V	_	_	1	V
f _T	transition frequency	I _C = 50 mA; V _{CE} = 10 V; f = 100 MHz	100	_	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	_	_	10	pF

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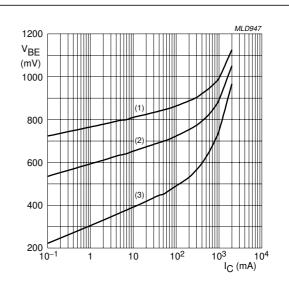
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 $\textbf{PSS8050C} \ V_{CE} = 1 \ V.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

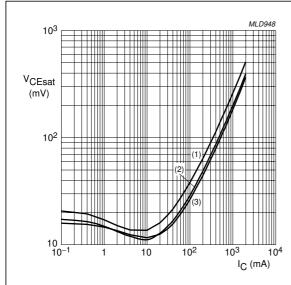
Fig.2 DC current gain as a function of collector current; typical values.



 $\textbf{PSS8050C} \ V_{CE} = 1 \ V.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

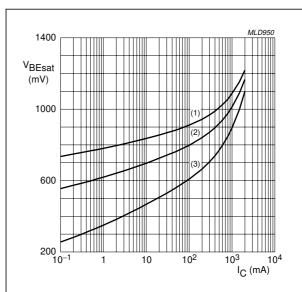
Fig.3 Base-emitter voltage as a function of collector current; typical values.



PSS8050C $I_C/I_B = 10$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



PSS8050C $I_{\text{C}}/I_{\text{B}} = 10.$

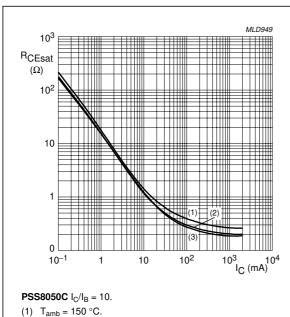
- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C.$
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

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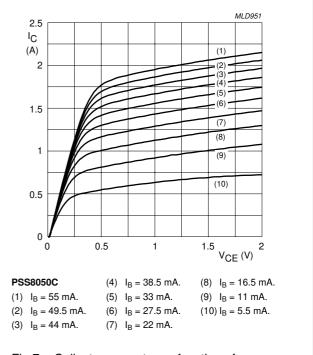
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- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

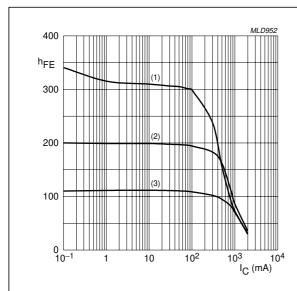
Fig.6 Equivalent on-resistance as a function of collector current; typical values.



Collector current as a function of collector-emitter voltage; typical values.

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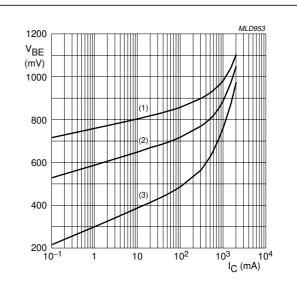
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PSS8050D V_{CE} = 1 V.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

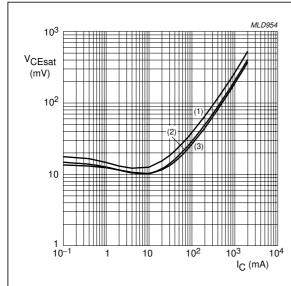
Fig.8 DC current gain as a function of collector current; typical values.



PSS8050D $V_{CE} = 1 V$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

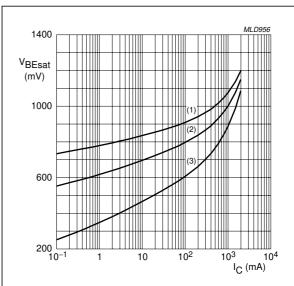
Fig.9 Base-emitter voltage as a function of collector current; typical values.



PSS8050D $I_C/I_B = 10$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.10 Collector-emitter saturation voltage as a function of collector current; typical values.



PSS8050D I_C/I_B = 10.

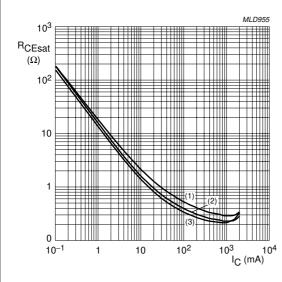
- (1) $T_{amb} = -55 \,^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.11 Base-emitter saturation voltage as a function of collector current; typical values.

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 $\textbf{PSS8050D} \ \textbf{I}_{C}/\textbf{I}_{B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.12 Equivalent on-resistance as a function of collector current; typical values.

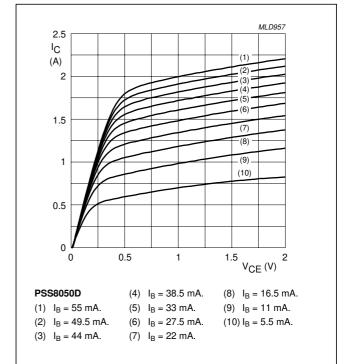


Fig.13 Collector current as a function of collector-emitter voltage; typical values.

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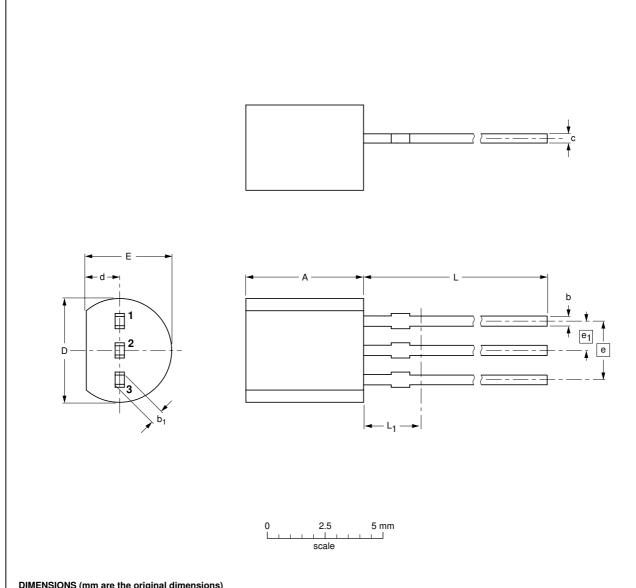
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE	OUTLINE REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			97-02-28 04-06-28

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LEVEL	DATA SHEET STATUS(1)	PRODUCT STATUS(2)(3)	DEFINITION
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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